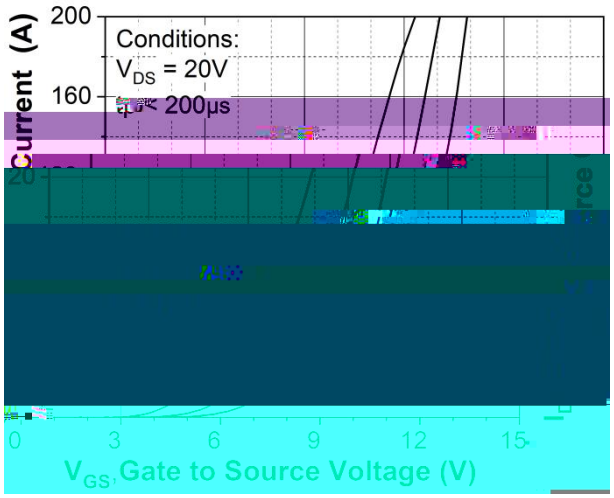
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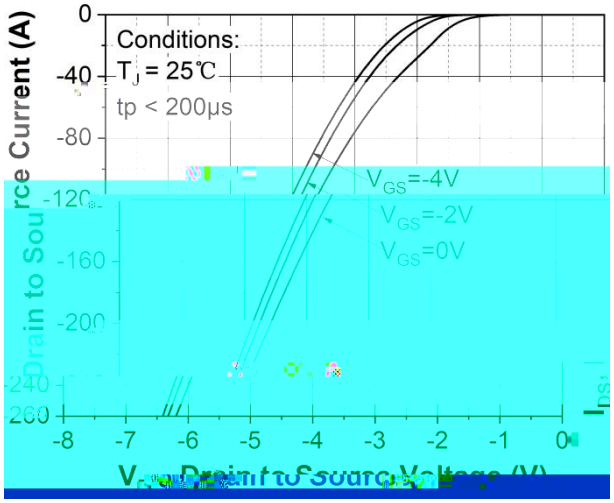
TO-247-4L

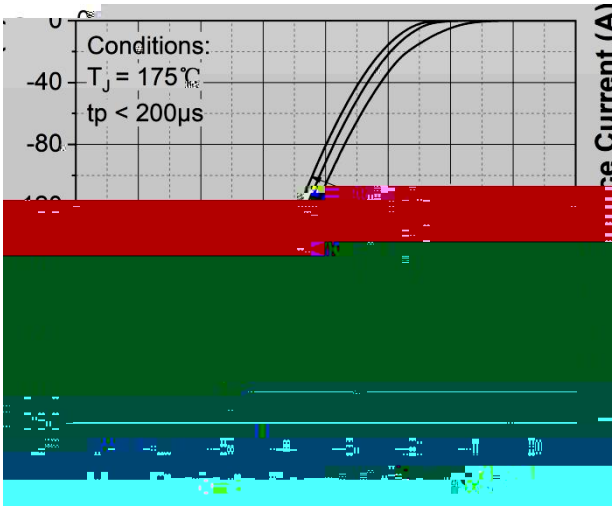
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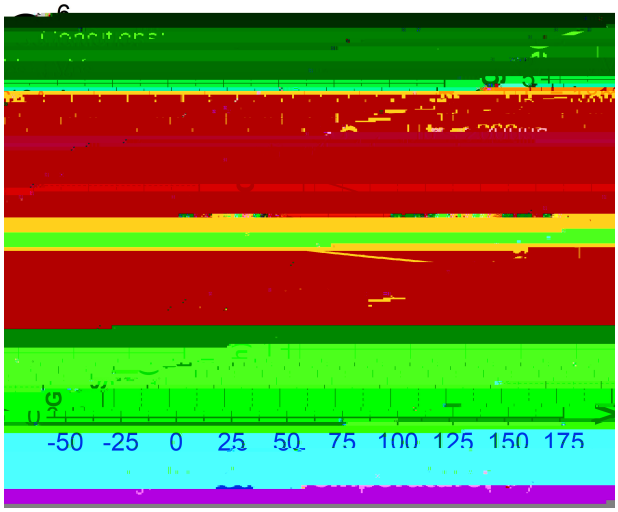
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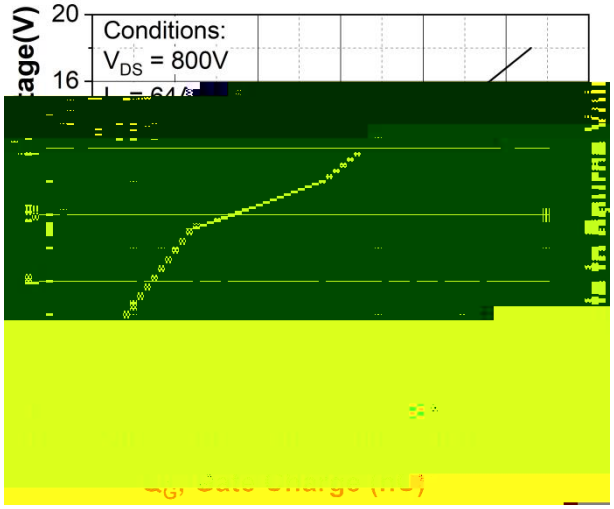

Conditions:
V_{DS} = 20V
tp < 200μs
Current (A)
200
160
0
3
6
9
12
15
V_{GS}, Gate to Source Voltage (V)

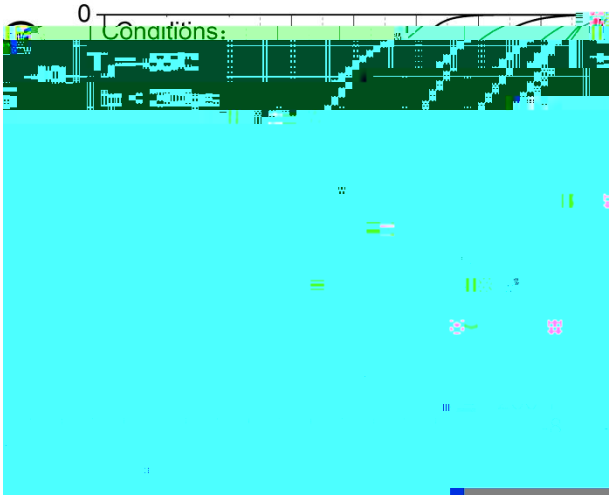

(A)
0
Conditions:

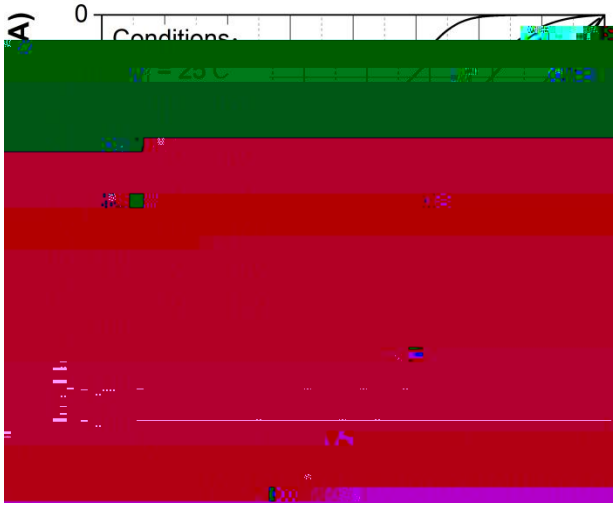

Conditions:
T_J = 25℃
tp < 200μs
V_{GS}=-4V
V_{GS}=-2V
V_{GS}=0V
Drain to Source Current (A)
0
-40
-80
-120
-160
-200
-240
-280
-8
-7
-6
-5
-4
-3
-2
-1
0

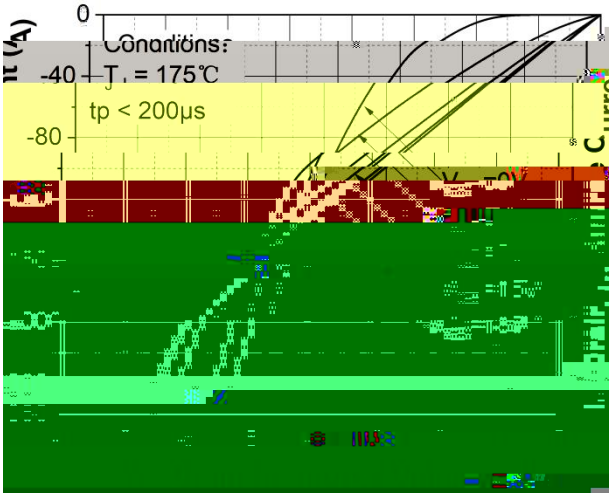

Conditions:
T_J = 175℃
tp < 200μs
-40
-80

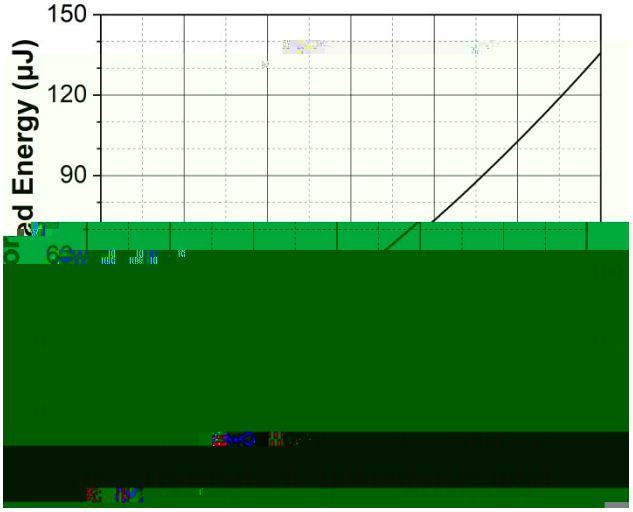

-50
-25
0
25
50
75
100
125
150
175


20
16
Conditions:
V_{DS} = 800V

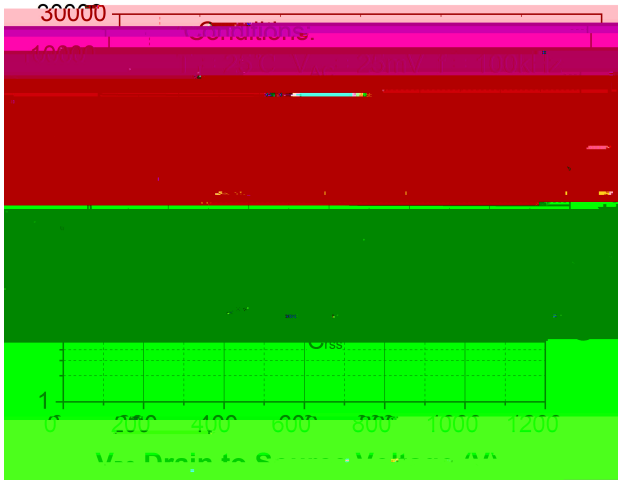

0
Conditions:

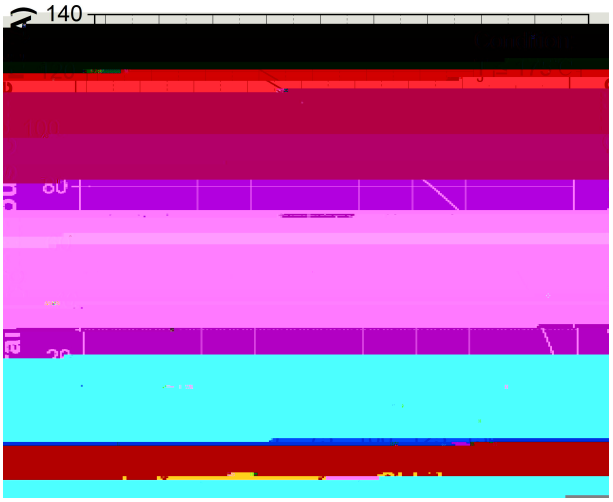

0
Conditions:

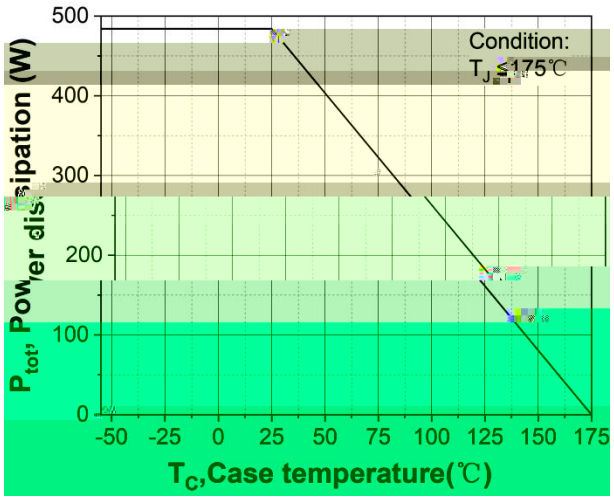

0
Conditions:
-40
tp < 200µs
-80

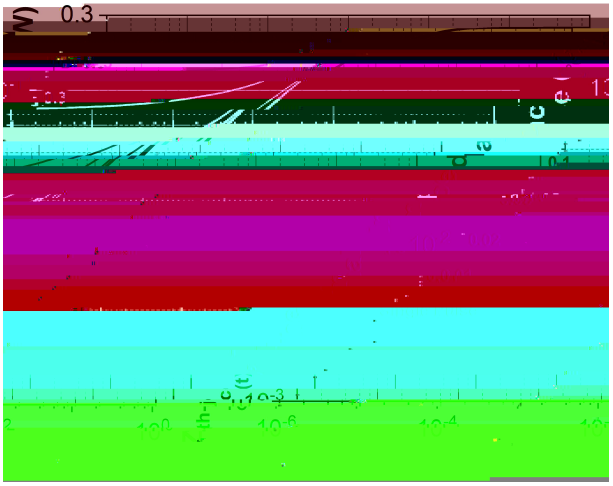

150
120
90

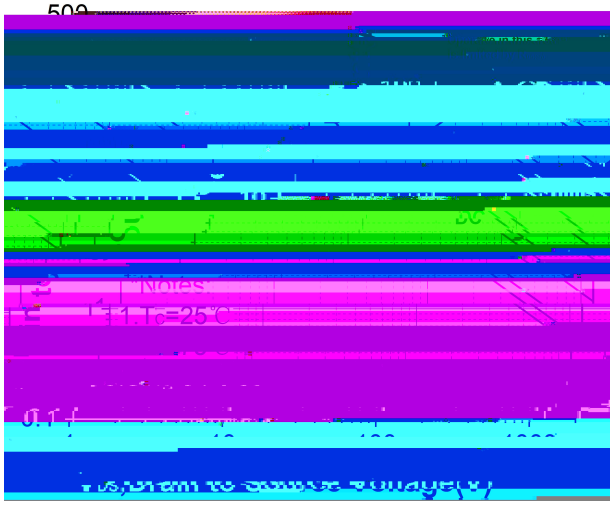

30000

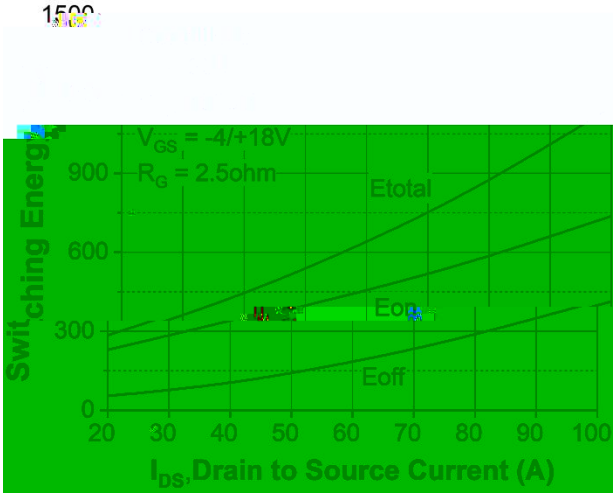

30000
1

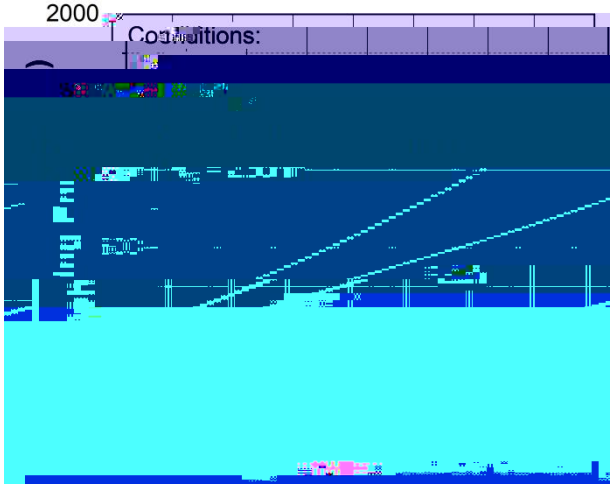

140

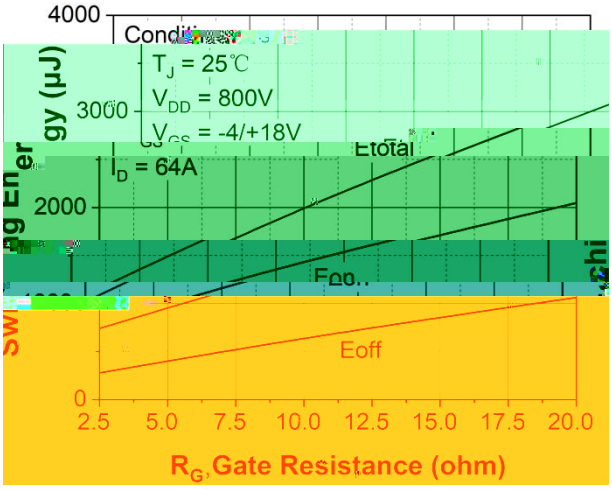

500
400
300
200
100
0
Condition:
$T_J \leq 175℃$
P_{tot}, Power dissipation (W)
-50 -25 0 25 50 75 100 125 150 175
T_C,Case temperature(℃)

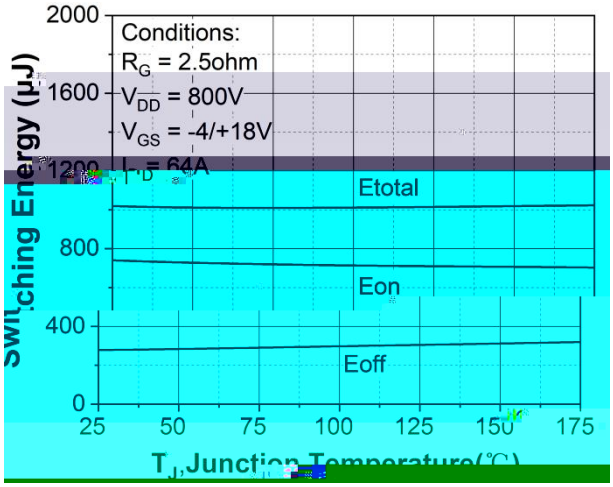

0.3

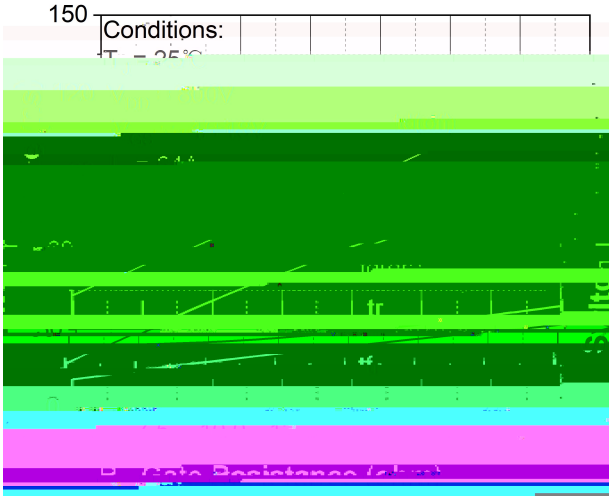

Notes:
T_C=25℃

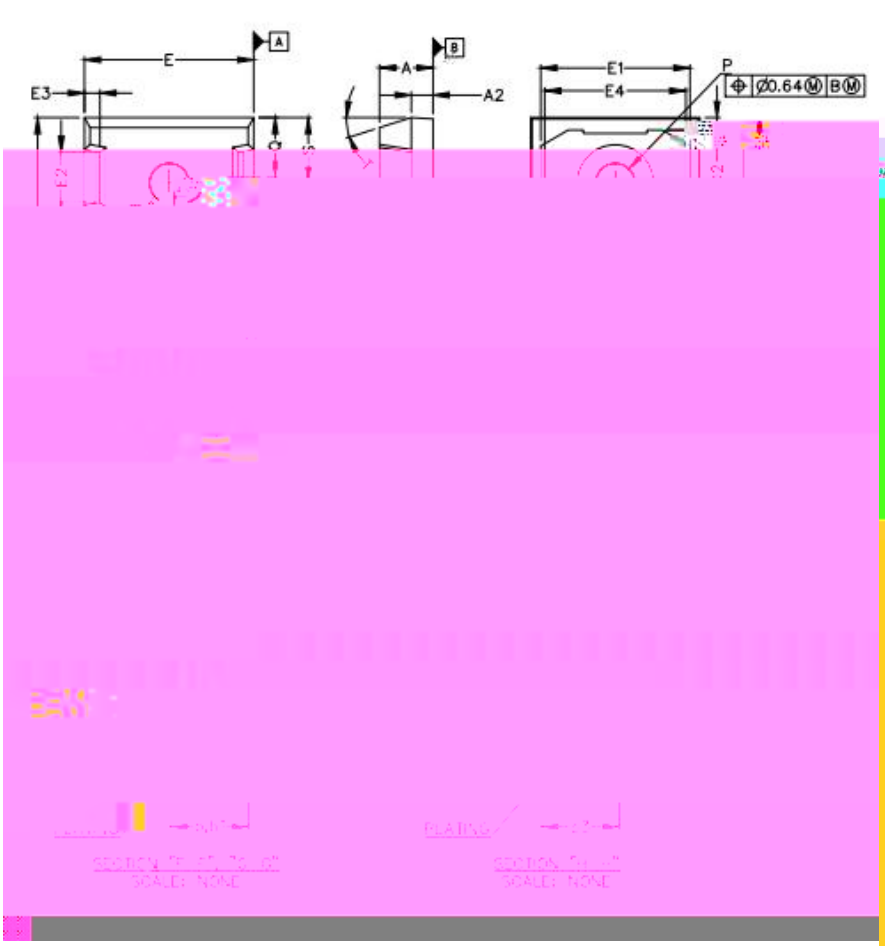

1500
V_{GS} = -4/+18V
R_G = 2.5ohm
900
600
300
0
Etotal
Eon
Eoff
Switching Energy
20 30 40 50 60 70 80 90 100
I_{DS},Drain to Source Current (A)


2000
Conditions:


4000
3000
2000
0
Conditions:
T_J = 25℃
V_{DD} = 800V
V_{GS} = -4/+18V
I_D = 64A
Etotal
Eoff
2.5
5.0
7.5
10.0
12.5
15.0
17.5
20.0
R_G, Gate Resistance (ohm)

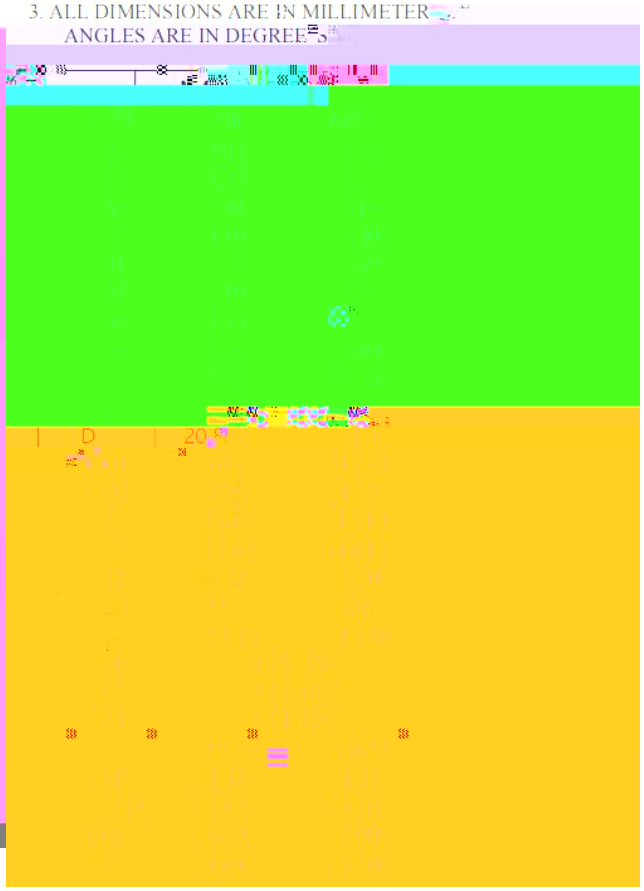

2000
1600
1200
800
400
0
Conditions:
R_G = 2.5ohm
V_{DD} = 800V
V_{GS} = -4/+18V
I_D = 64A
Etotal
Eon
Eoff
25
50
75
100
125
150
175
T_J, Junction Temperature(℃)

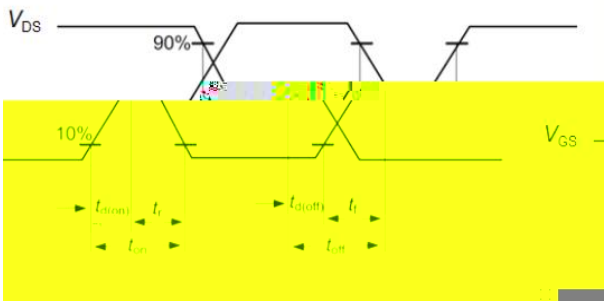

150
Conditions:

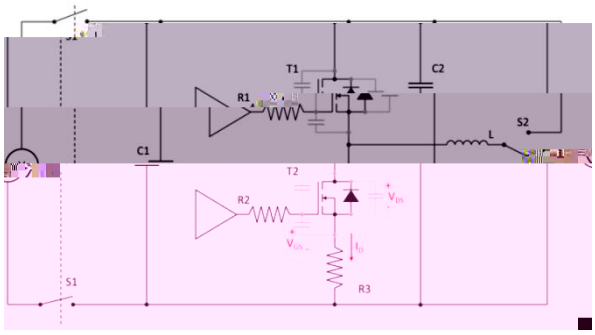


NOTE ;

1. ALL METAL SURFACES: TIN PLATED,EXCEPT AREA OF CUT
2. DIMENSIONING & TOLERANCEING CONFIRM TO ASME Y14.5M-1994.
3. ALL DIMENSIONS ARE IN MILLIMETERS.
   ANGLES ARE IN DEGREES.




V_{DS}
90%
10%
V_{GS}
$t_{d(on)}$
t_r
t_{on}
$t_{d(off)}$
t_f
t_{off}


T1
C2
R1
S2
L
C1
T2
R2
R3
S1